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November 2013

FQP27N25

N-Channel QFET[®] MOSFET 250 V, 25.5 A, 110 m Ω

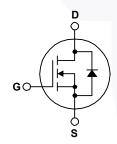
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

Features

- 25.5 A, 250 V, $R_{DS(on)}$ = 110 m Ω (Max.) @ V_{GS} = 10 V, I_D = 12.75 A
- Low Gate Charge (Typ. 50 nC)
- · Low Crss (Typ. 45 pF)
- · 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP27N25	Unit
V_{DSS}	Drain-Source Voltage		250	V
I _D	Drain Current - Continuous (T _C = 25°C))	25.5	А
	- Continuous (T _C = 100°C	C)	16.2	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	102	A
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	600	mJ
I _{AR}	Avalanche Current	(Note 1)	25.5	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	18	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
P _D	Power Dissipation (T _C = 25°C)		180	W
	- Derate above 25°C		1.43	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQP27N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP27N25	FQP27N25	TO-220	Tube	N/A	N/A	50 units

Electrical Characteristics

T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Uni
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	250			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.29		V/°(
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 250 V, V _{GS} = 0 V			1	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 200 V, T _C = 125°C			10	μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	n/
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 12.75 A		0.083	0.11	Ω
0	Forward Transconductance	V _{DS} = 50 V, I _D = 12.75 A		24		S
9FS	1 orward framedoridation	B0 · B				U
Dynam	ic Characteristics					
Dynam C _{iss}		V _{DS} = 25 V, V _{GS} = 0 V,		1900	2450	
Dynam C _{iss} C _{oss}	ic Characteristics	30 3			2450 470	pF
9FS Dynam C _{iss} C _{oss} C _{rss}	ic Characteristics Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		1900		pF pF
Dynam C _{iss} C _{oss} C _{rss}	ic Characteristics Input Capacitance Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		1900 360	470	pF pF
Dynam C _{iss} C _{oss} C _{rss}	ic Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz		1900 360	470	pF pF
Dynam C _{iss} C _{oss} C _{rss} Switch	ic Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance ing Characteristics	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1.0 \text{ MHz}$ $V_{DD} = 125 \text{ V}, I_{D} = 27 \text{ A},$		1900 360 45	470 60	pF pF pF
Dynam C _{iss} C _{oss} C _{rss} Switch	ic Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance ing Characteristics Turn-On Delay Time	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1.0 \text{ MHz}$ $V_{DD} = 125 \text{ V}, I_{D} = 27 \text{ A},$ $R_{G} = 25 \Omega$		1900 360 45	470 60 75	pF pF pF
Dynam C _{iss} C _{oss} C _{rss} Switch t _{d(on)} t _r t _{d(off)}	ic Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance ing Characteristics Turn-On Delay Time Turn-On Rise Time	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1.0 \text{ MHz}$ $V_{DD} = 125 \text{ V}, I_{D} = 27 \text{ A},$		1900 360 45 32 270	470 60 75 550	pF pF pF
$\begin{array}{c} \textbf{Dynam} \\ C_{iss} \\ C_{oss} \\ C_{rss} \\ \textbf{Switch} \\ \\ ^{t_{d(on)}} \\ t_{r} \\ \\ ^{t_{d(off)}} \\ \end{array}$	ic Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance ing Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1.0 \text{ MHz}$ $V_{DD} = 125 \text{ V}, I_{D} = 27 \text{ A},$ $R_{G} = 25 \Omega$	 	1900 360 45 32 270 80	470 60 75 550 170	pF pF pF
Dynam C _{iss} C _{oss} C _{rss}	ic Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance ing Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz $V_{DD} = 125 \text{ V}, I_D = 27 \text{ A},$ $R_G = 25 \Omega$ (Note 4)	 	1900 360 45 32 270 80 120	470 60 75 550 170 250	pF pF

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current				25.5	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				102	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 25.5 A			1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 27 A,		220		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		1.8		μC

- **Notes:** 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = 1.5 mH, I $_{AS}$ = 25.5 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C. 3. I $_{SD}$ \leq 27 A, di/dt \leq 300 A μ I $_{IS}$, V $_{DD}$ \leq BV $_{DSS}$, starting T $_{J}$ = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

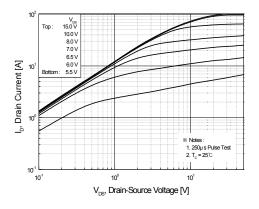
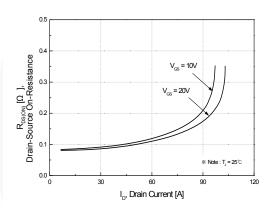


Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



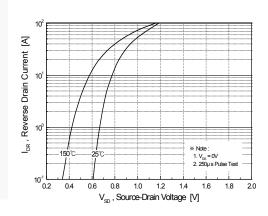
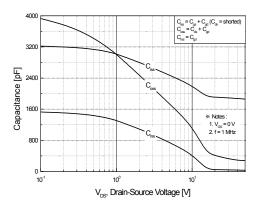


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



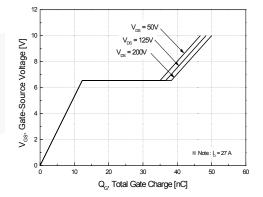
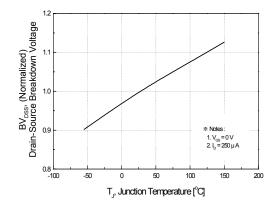


Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

Typical Characteristics (continued)



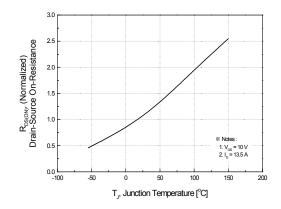
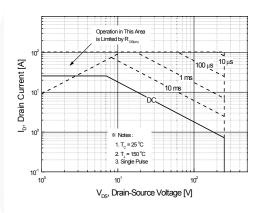


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



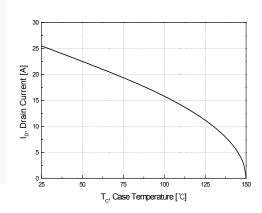


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

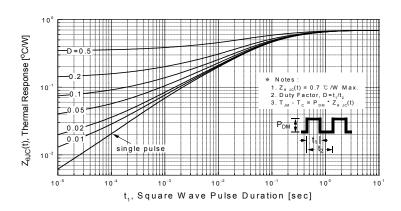


Figure 11. Transient Thermal Response Curve

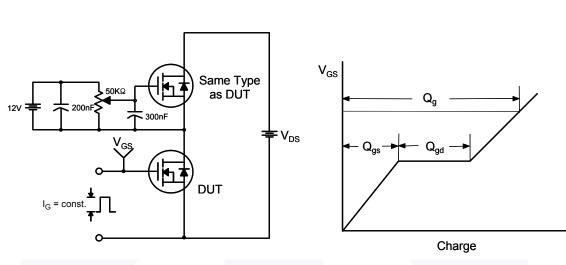


Figure 12. Gate Charge Test Circuit & Waveform

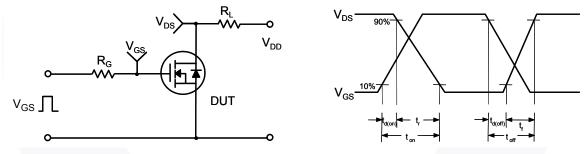


Figure 13. Resistive Switching Test Circuit & Waveforms

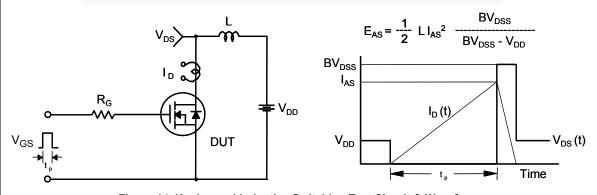
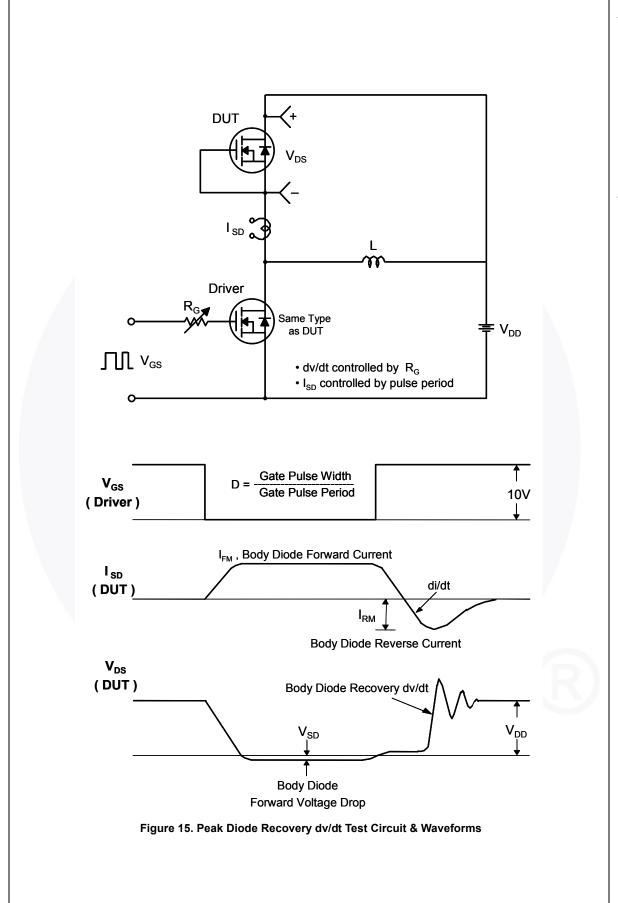
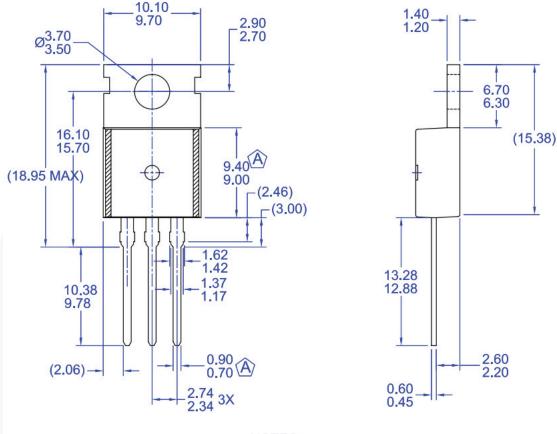


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions



4.70 10.20 9.80

NOTES:

- (A) CONFORMS TO JEDEC TO-220 VARIATION AB EXCEPT WHERE NOTED
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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